

SOT-23 Plastic-Encapsulate Transistors

MMBTA56 (NPN)

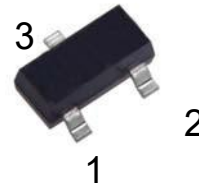
Features:

- ☐ High Stability and High Reliability
- ☐ Power Dissipation of 225mW
- ☐ Complementary to MMBTA06

Marking:2GM



SOT-23



- 1.Base (B)
2. Emitter (E)
3.Collector (C)

Maximum Ratings & Thermal Characteristics (Ratings at 25°C ambient temperature unless otherwise specified.)

Parameters	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V _{CEO}	-80	V
Emitter -Base Voltage	V _{EBO}	-4	V
Collector Current-Continuous	I _C	-500	mA
Collector Power Dissipation	P _C	225	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55-+150	°C
Thermal resistance From junction to ambient	R _{θJA}	555	°C/W

Electrical Characteristics (Ratings at 25°C ambient temperature unless otherwise specified).

参数 Parameter	符号 Symbols	测试条件 Test Condition	界限 Limits		单位 Unit
			Min	Max	
Collector-base breakdown voltage	V(BR)CBO	I _C =-100uA, I _E =0	-80		V
Collector-emitter breakdown voltage	V(BR)CEO *	I _C =-1mA, I _B =0	-80		V
Emitter-base breakdown voltage	V(BR)EBO	I _E =-100uA, I _C =0	-4		V
Collector cut-off current	I _{CBO}	V _{CB} =-80V, I _E =0		-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0		-100	nA
Collector cut-off current	I _{CE0}	V _{CE} =-60V, I _B =0		-1.0	uA
DC current gain	hFE(1) *	V _{CE} =-1V, I _C =-10mA	100	400	
	hFE(2) *	V _{CE} =-1V, I _C =-100mA	100		
Collector-emitter saturation voltage	V _{CE(sat)} *	I _C =-100mA, I _B =-10mA		-0.25	V
Base -emitter voltage	V _{BE}	V _{CE} =-1V, I _C =-100mA		-1.20	V
Transition frequency	f _T	V _{CE} =-1V, I _C =-100mA, f=100MHz	50		MHz

*Pulse test: pulse width ≤ 300us, duty cycle ≤ 2.0%

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Typical Characteristics

